

Complementary power transistors

Features

- Low collector-emitter saturation voltage
- Complementary NPN - PNP transistors

Applications

- General purpose
- Audio amplifier

Description

The devices are manufactured in planar technology with "base island" layout. The resulting transistors show exceptional high gain performance coupled with very low saturation voltage.

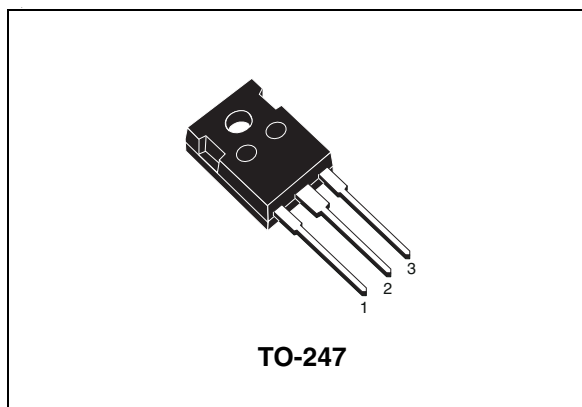


Figure 1. Internal schematic diagrams

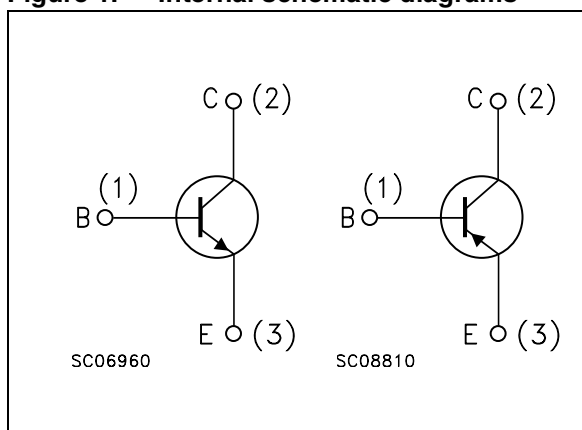


Table 1. Device summary

Order code	Marking	Package	Packaging
TIP35C	TIP35C	TO-247	Tube
TIP36C	TIP36C		

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter		Value	Unit
		NPN	TIP35C	
		PNP	TIP36C	
V_{CBO}	Collector-base voltage ($I_E = 0$)		100	V
V_{CEO}	Collector-emitter voltage ($I_B = 0$)		100	V
V_{EBO}	Emitter-base voltage ($I_C = 0$)		5	V
I_C	Collector current		25	A
I_{CM}	Collector peak current ($t_P < 5$ ms)		50	A
I_B	Base current		5	A
P_{tot}	Total dissipation at $T_{case} = 25$ °C		125	W
T_{stg}	Storage temperature		-65 to 150	°C
T_J	Max. operating junction temperature		150	°C

For PNP type voltage and current values are negative.

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	1	°C/W

2 Electrical characteristics

($T_{\text{case}} = 25\text{ }^{\circ}\text{C}$; unless otherwise specified)

Table 4. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{CEO}	Collector cut-off current ($I_{\text{B}} = 0$)	$V_{\text{CE}} = 60\text{ V}$			1	mA
I_{EBO}	Emitter cut-off current ($I_{\text{C}} = 0$)	$V_{\text{EB}} = 5\text{ V}$			1	mA
I_{CES}	Collector cut-off current ($V_{\text{BE}} = 0$)	$V_{\text{CE}} = 100\text{ V}$			0.7	mA
$V_{\text{CEO(sus)}}^{(1)}$	Collector-emitter sustaining voltage ($I_{\text{B}} = 0$)	$I_{\text{C}} = 30\text{ mA}$	100			V
$V_{\text{CE(sat)}}^{(1)}$	Collector-emitter saturation voltage	$I_{\text{C}} = 15\text{ A}$ $I_{\text{B}} = 1.5\text{ A}$			1.8	V
		$I_{\text{C}} = 25\text{ A}$ $I_{\text{B}} = 5\text{ A}$			4	V
$V_{\text{BE(on)}}^{(1)}$	Base-emitter voltage	$I_{\text{C}} = 15\text{ A}$ $V_{\text{CE}} = 4\text{ V}$			2	V
		$I_{\text{C}} = 25\text{ A}$ $V_{\text{CE}} = 4\text{ V}$			4	V
$h_{\text{FE}}^{(1)}$	DC current gain	$I_{\text{C}} = 1.5\text{ A}$ $V_{\text{CE}} = 4\text{ V}$	25		50	
		$I_{\text{C}} = 15\text{ A}$ $V_{\text{CE}} = 4\text{ V}$	10			
f_{T}	Transition frequency	$I_{\text{C}} = 1\text{ A}$ $V_{\text{CE}} = 10\text{ V}$ $f = 1\text{ MHz}$	3			MHz

1. Pulsed duration = 300 ms, duty cycle $\geq 1.5\%$.

For PNP type voltage and current are negative.

2.1 Electrical characteristic (curves)

Figure 2. DC current gain for NPN type Figure 3. DC current gain for PNP type

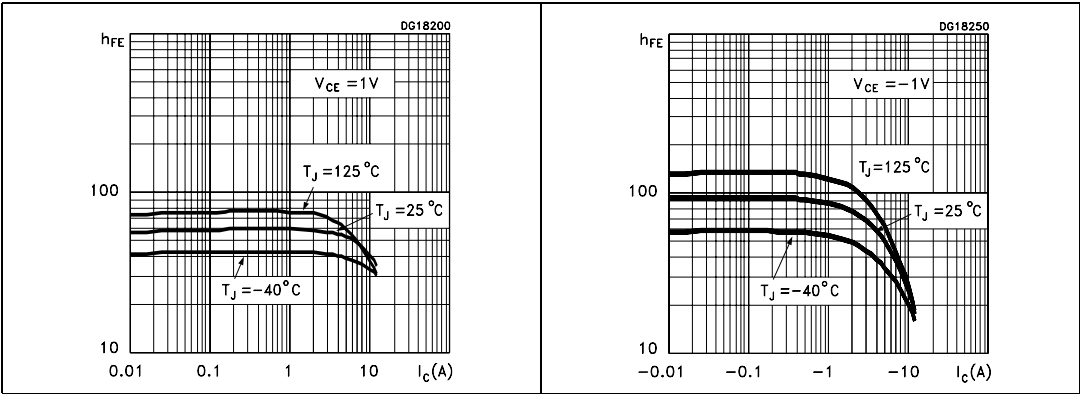


Figure 4. DC current gain for NPN type Figure 5. DC current gain for PNP type

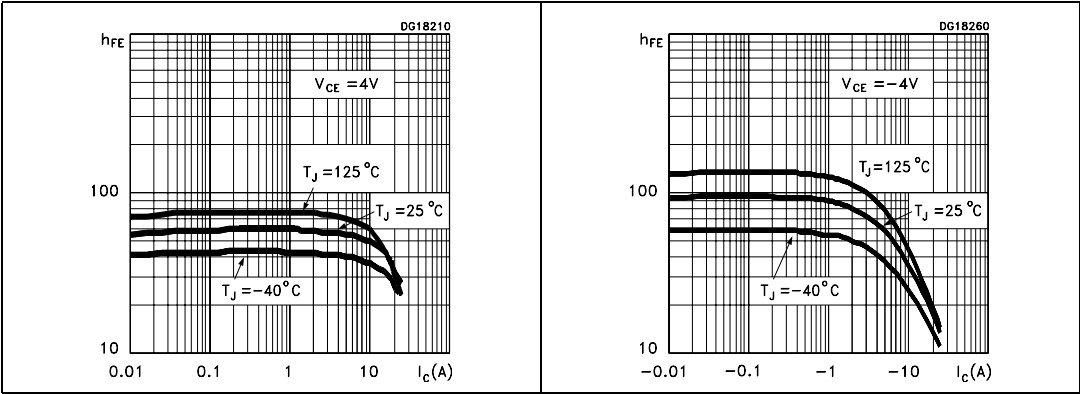


Figure 6. Collector-emitter saturation voltage for NPN type Figure 7. Collector-emitter saturation voltage for PNP type

